MY10N65D

650V N-Channel Enhancement Mode MOSFET

MAOYUANWEI semiconductor

General Description

The MY10N65D is silicon N-channel Enhanced VDMOSFETs, obtained by the self-aligned planar Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy.

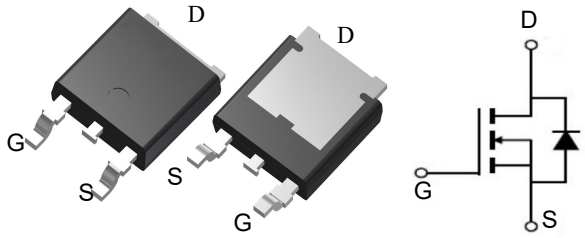
RoHS Compliant

Features

V_{DSS}	650	V
I_D	10	A
P_D(T_C= 2 5℃)	53	W
$R_{DS(ON)}$(atV_{GS} = 10V)	85	mΩ

Application

- High efficiency switch mode power supplies
- Power factor correction
- Electronic lamp ballast



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY10N65D	TO-252	MY10N65D	1000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameters	Ratings	Unit
V_{DSS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage-Continuous	±30	V
I_D	Drain Current-Continuous（Note 2）	10	A
I_{DM}	Drain Current-Single Plused（Note 1）	38	A
P_D	Power Dissipation （Note 2）	53	W
T_j	Max.Operating junction temperature	150	℃/W

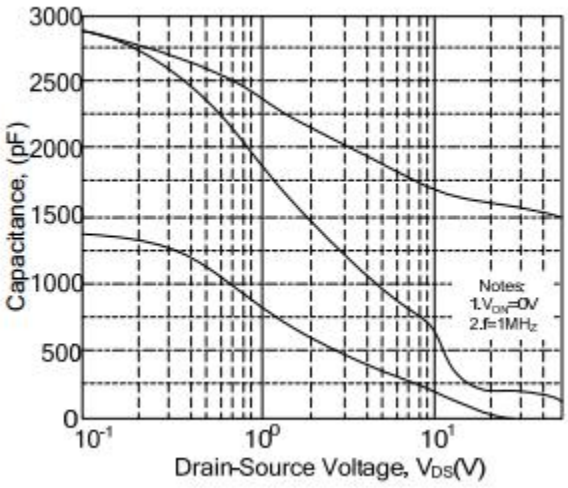
Electrical Characteristics (T_C=25 ℃, unless otherwise noted)

Symbol	Parameters	Min	Typ	Max	Units	Conditions
Static Characteristics						
B_{VDSS}	Drain-Source Breakdown VoltageCurrent （Note 1）	650	--	--	mA	I_D=250μA V_{GS}=0V， T_J=25°C
$V_{GS(th)}$	Gate Threshold Voltage	2.0	--	4.0	V	V_{DS}=V_{GS}， I_D=250μA
$R_{DS(on)}$	Drain-Source On-Resistance	--	85	100	mΩ	V_{GS}=10V， I_D=5A
I_{GSS}	Gate-Body Leakage Current	--	--	±100	nA	V_{GS}=±30V， V_{DS}=0
I_{DSS}	Zero Gate Voltage Drain Current	--	--	1	μA	V_{DS}=650V， V_{GS}=0
Switching Characteristics						
$T_{d\ (on)}$	Turn-On Delay Time	--	23	55	ns	V_{DS}=325V， I_D=10A， R_G=25Ω（Note 2）
T_r	Rise Time	--	69	150	ns	
$T_{d\ (off)}$	Turn-Off Delay Time	--	144	300	ns	
T_f	Fall Time	--	77	165	ns	
Qg	Total Gate Charge	--	44	57	nC	V_{DS}=520 , V_{GS}=10V， I_D=10A （Note 2）
Qgs	Gate-Source Charge	--	6.7	--	nC	
Qgd	Gate-Drain Charge	--	18.5	--	nC	
Dynamic Characteristics						
Ciss	Input Capacitance	--	1570	2040	pF	V_{DS}=25V， V_{GS}=0， f=1MHz
Coss	Output Capacitance	--	166	215	pF	
Crss	Reverse Transfer Capacitance	--	18	24	pF	
I_S	Continuous Drain-Source Diode ForwardCurrent （Note 2）	--	--	10	A	
V_{SD}	Diode Forward On-Voltage	--	--	1.4	V	I_S=10A， V_{GS}=0
$R_{th(j-c)}$	Thermal Resistance, Junction to Case	--	--	0.85	°C/W	

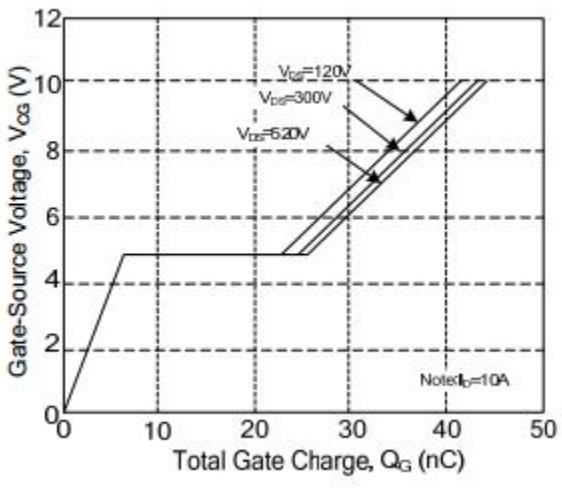
Note 1: Repetitive Rating : Pulse width limited by maximum junction temperature
Note 2: Pulse test: PW <= 300us , duty cycle <= 2%.

Ratings and Characteristic curves

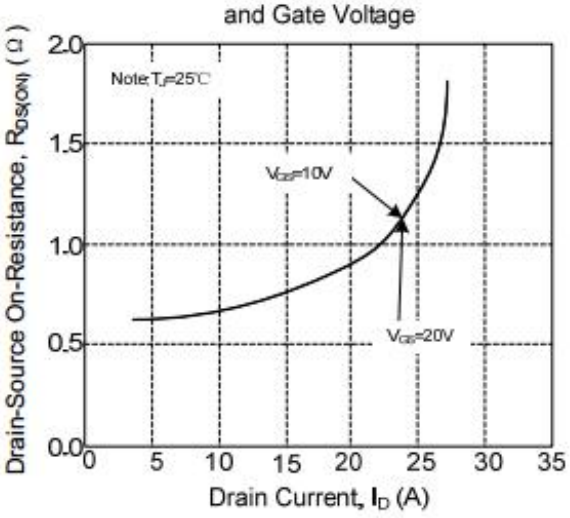
Capacitance Characteristics



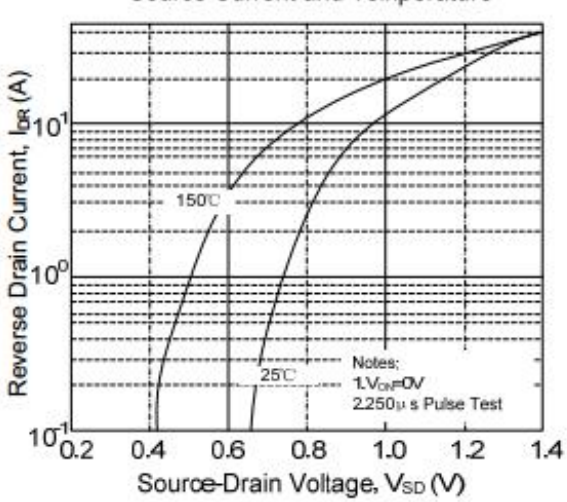
Gate Charge Characteristics



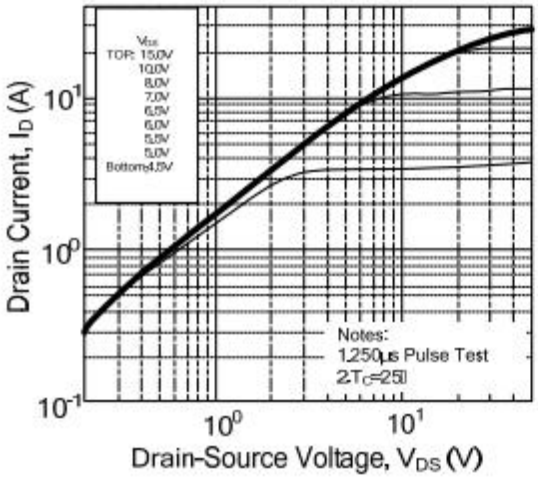
On-Resistance Variation vs. Drain Current and Gate Voltage



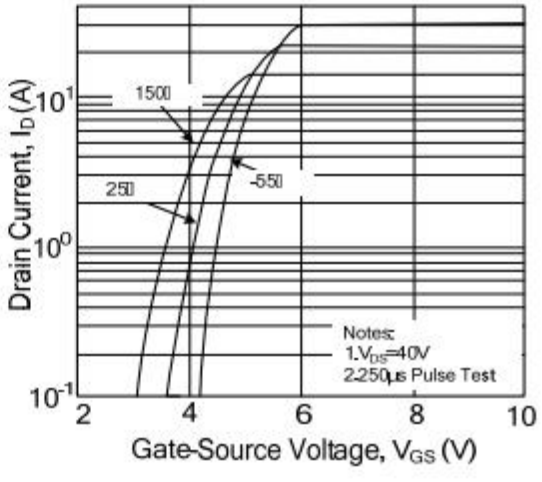
Body Diode Forward Voltage Variation with Source Current and Temperature



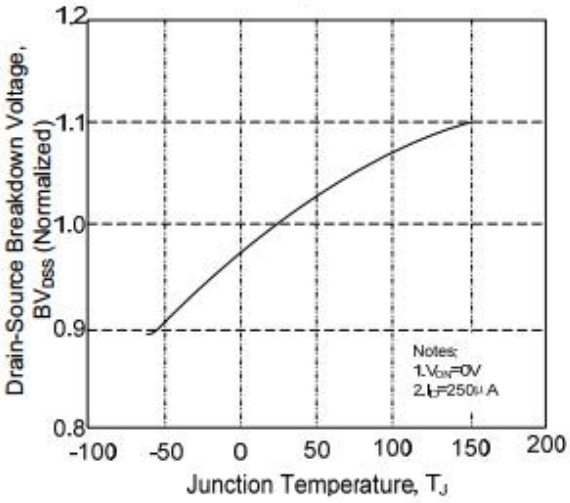
On-Region Characteristics



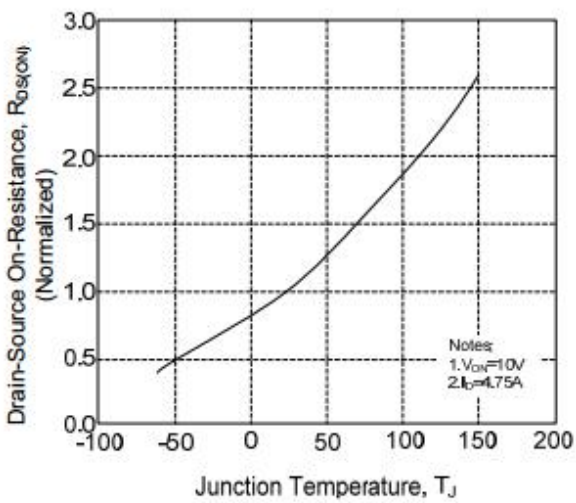
Transfer Characteristics



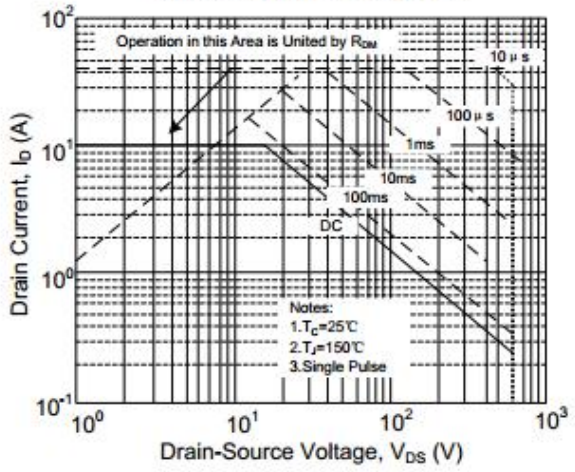
Breakdown Voltage Variation vs. Temperature



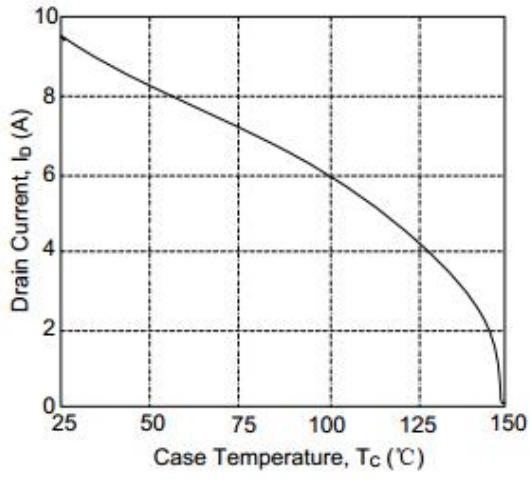
On-Resistance Variation vs. Temperature



Maximum Safe Operating Area



Maximum Drain Current vs. Case Temperature



Transient Thermal Response Curve

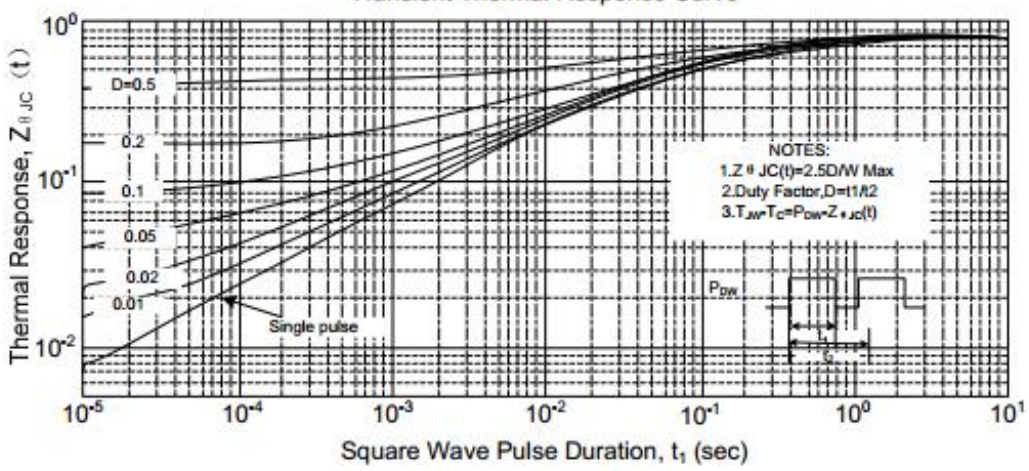


Fig 12. Gate Charge Test Circuit & Waveform

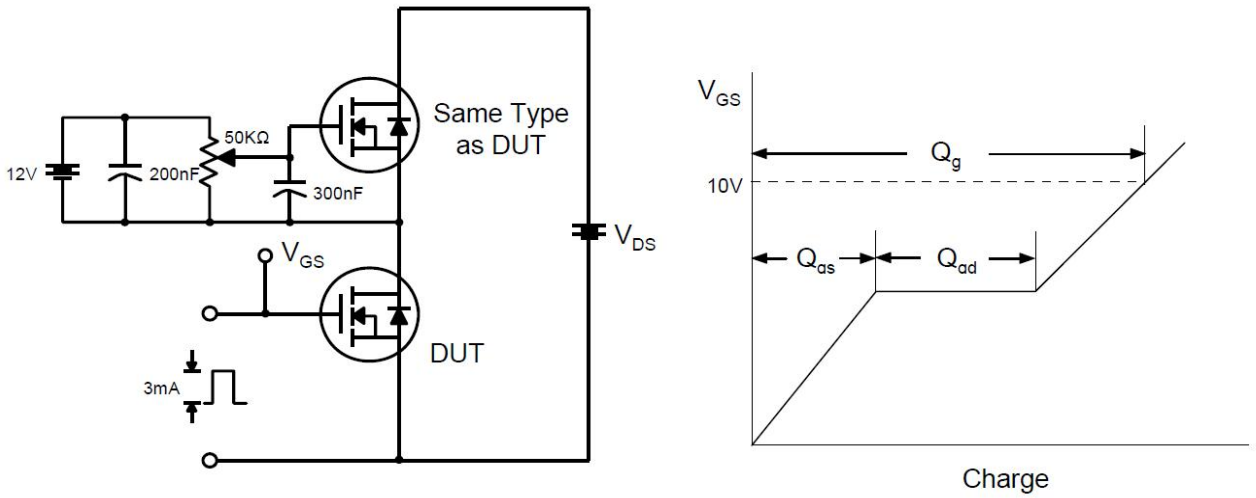


Fig 13. Resistive Switching Test Circuit & Waveforms

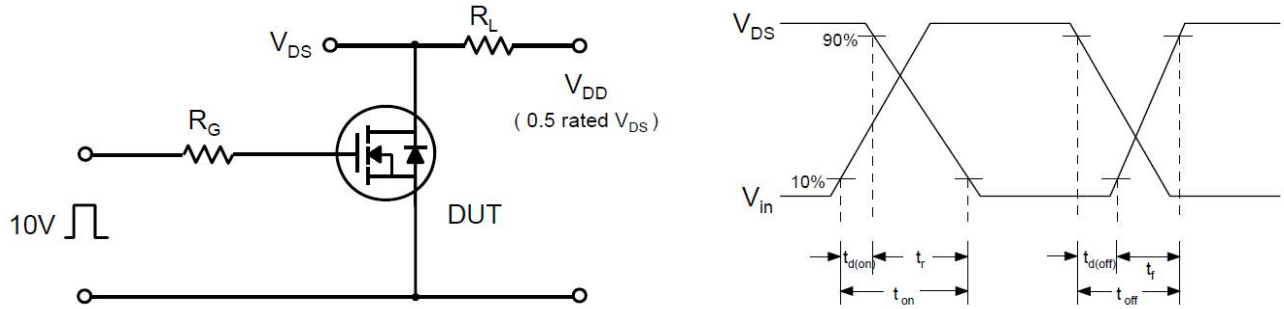


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

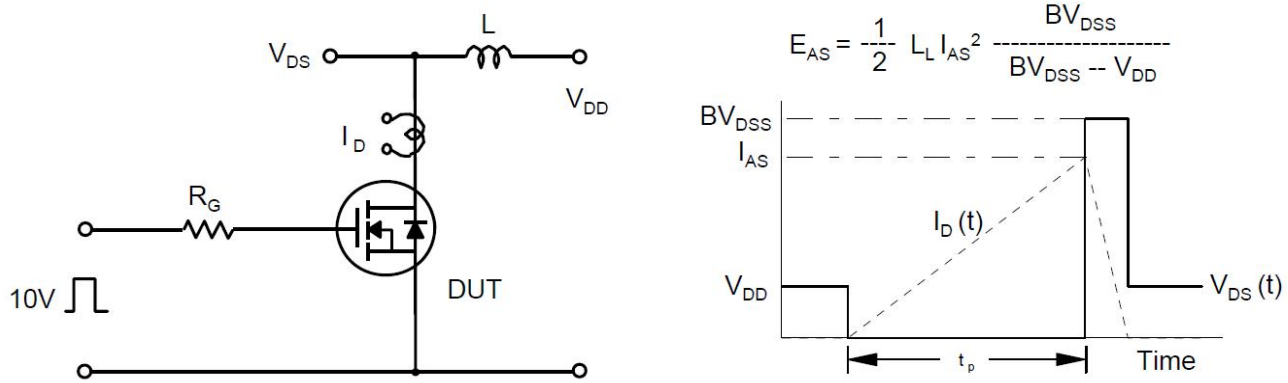
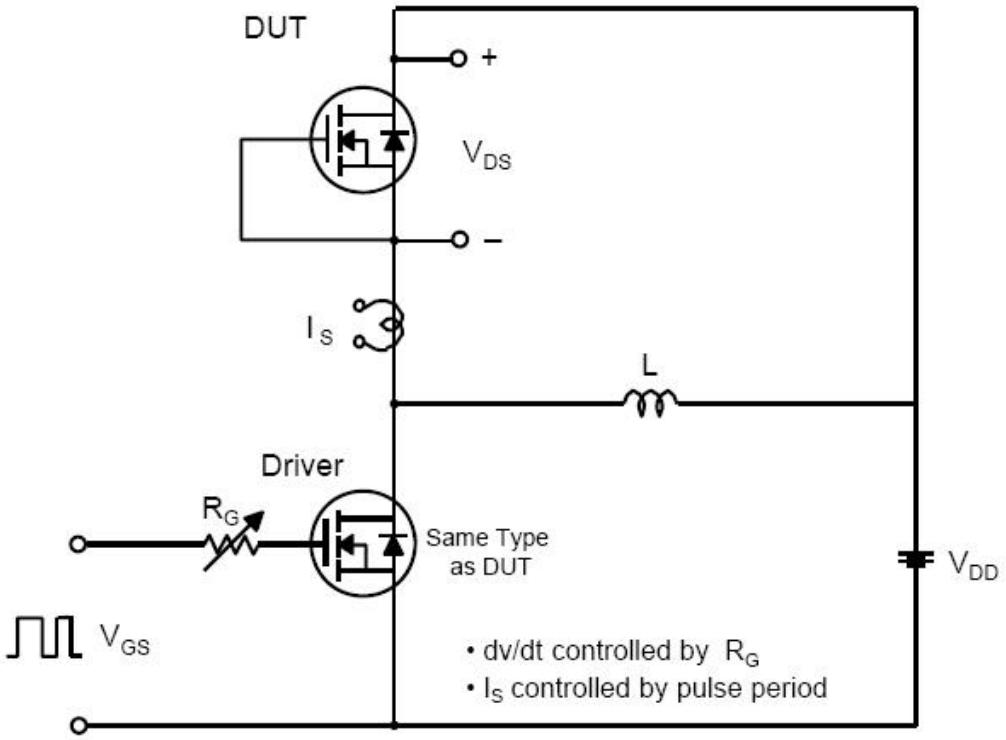
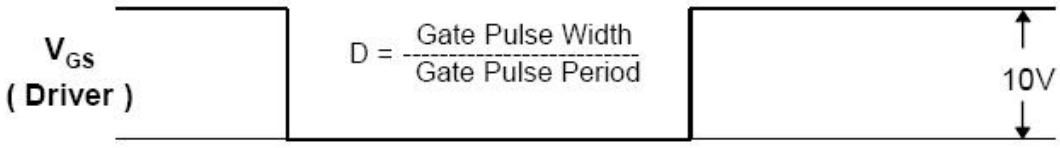
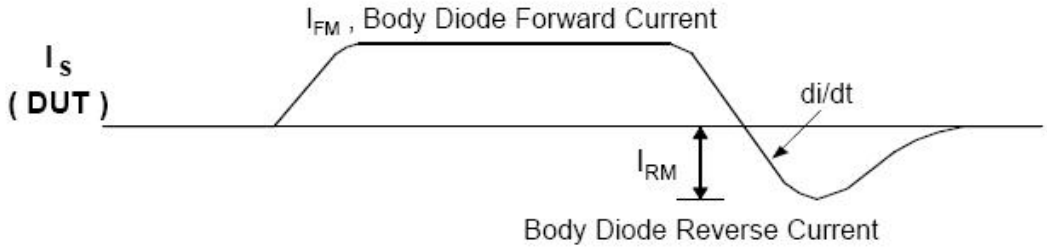
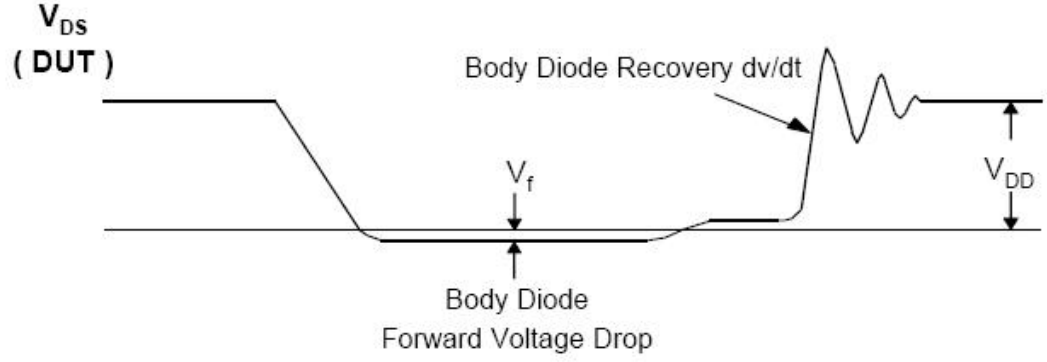


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

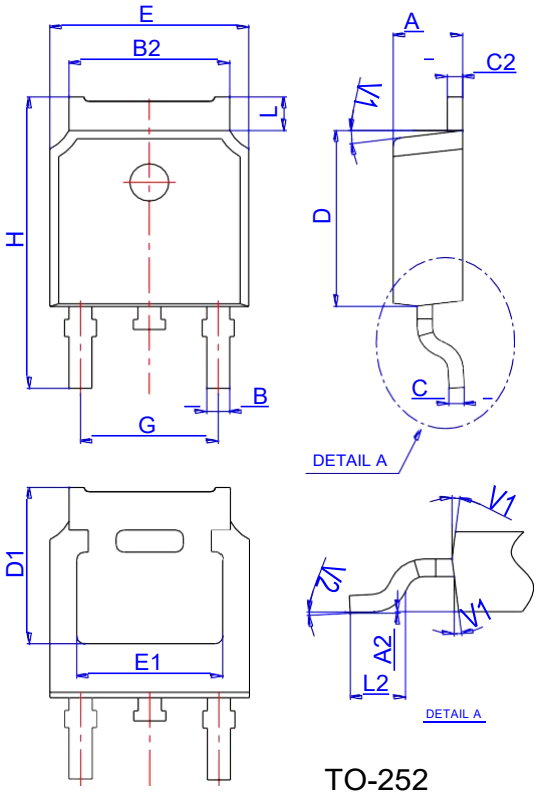








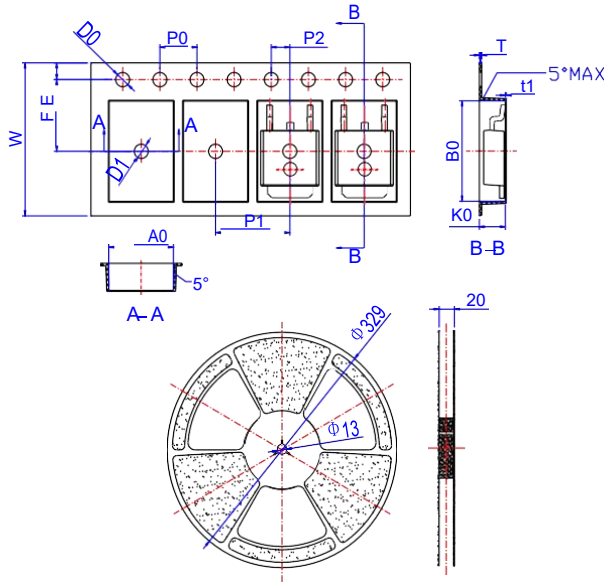
Package Mechanical Data-TO-252-JQ Single



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583